

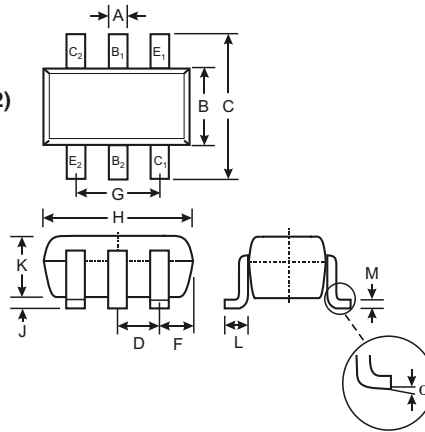
Features

- Epitaxial Planar Die Construction
- Built-In Biasing Resistors
- One 500mA PNP and One 100mA NPN
- Available in Lead Free/RoHS Compliant Version (Note 2)

Mechanical Data

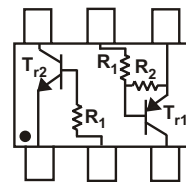
- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Also available in Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe). Please see Ordering Information, Note 4, on Page 2
- Marking Code: C73 (See Page 2)
- Ordering & Date Code: See Page 2
- Terminal Connections: See Diagram
- Weight: 0.015 grams (approx.)

P/N	R1	R2
MIMD10A	Tr1 Tr2	0.1K 10K



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°

All Dimensions in mm



SCHEMATIC DIAGRAM

Maximum Ratings PNP Section Tr1 @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V_{CC}	-50	V
Input Voltage	V_{IN}	-5 to +5	V
Output Current	I_O	-500	mA

Maximum Ratings NPN Section Tr2 @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA

Maximum Ratings - Total @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1)	P_d	200	mW
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 1. Mounted on FR4 PC Board with recommended pad layout at <http://www.diodes.com/datasheets/ap02001.pdf>.
2. No purposefully added lead.

Electrical Characteristics PNP Section Tr1 @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	V _{I(off)}	-0.3	—	—	V	V _{CC} = -5V, I _O = -100μA
	V _{I(on)}	—	—	-1.5		V _O = 0.3, I _O = -100mA
Output Voltage	V _{O(on)}	—	-0.1	-0.3	V	I _O = -100mA/-5mA
Input Current	I _I	—	—	-25	mA	V _I = -2V
Output Current	I _{O(off)}	—	—	-0.5	μA	V _{CC} = -50V, V _I = 0V
DC Current Gain	G _I	68	—	—	—	—
Gain-Bandwidth Product*	f _T	—	200	—	MHz	V _{CE} = -10V, I _E = -50mA, f = 100MHz

* Transistor - For Reference Only

Electrical Characteristics NPN Section Tr2 @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CB0}	50	—	—	V	I _C = 50μA
Collector-Emitter Breakdown Voltage	BV _{CEO}	50	—	—	V	I _C = 1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	5	—	—	V	I _E = 50μA
Collector Cutoff Current	I _{CB0}	—	—	0.5	μA	V _{CB} = 50V
Emitter Cutoff Current	I _{EBO}	—	—	0.5	μA	V _{EB} = 4V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	—	0.3	V	I _C /I _B = 10mA / 1.0mA
DC Current Transfer Ratio	h _{FE}	100	250	600	—	I _C = 1mA, V _{CE} = 5V
Gain-Bandwidth Product*	f _T	—	250	—	MHz	V _{CE} = 10V, I _E = -5mA, f = 100MHz

* Transistor - For Reference Only

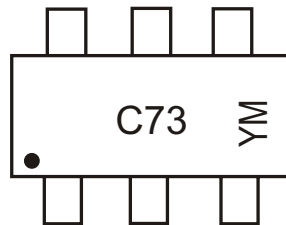
Ordering Information (Note 3)

Device	Packaging	Shipping
MIMD10A-7	SOT-363	3000/Tape & Reel

Notes: 3. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

4. For Lead Free/RoHS Compliant version part number, please add "-F" suffix to the part number above. Example: MIMD10A-7-F.

Marking Information



C73 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: P = 2003
 M = Month ex: 9 = September

Date Code Key

Year	2003	2004	2005	2006	2007	2008	2009	2010	2011
Code	P	R	S	T	U	V	W	X	Y

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

TYPICAL CURVES - Tr2

NEW PRODUCT

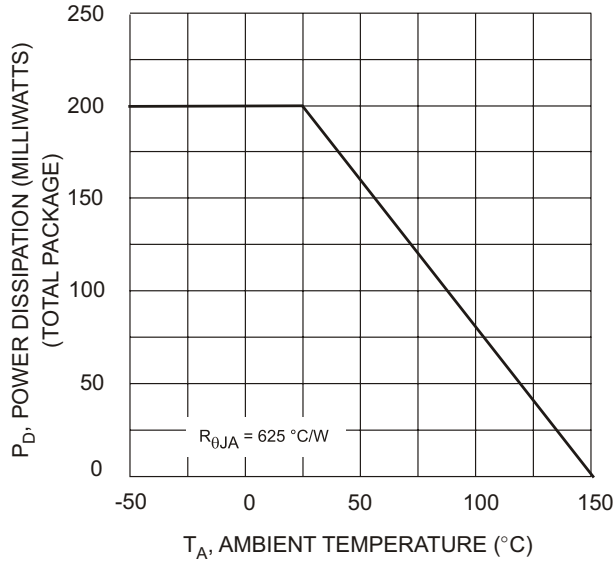


Fig. 1 Derating Curve

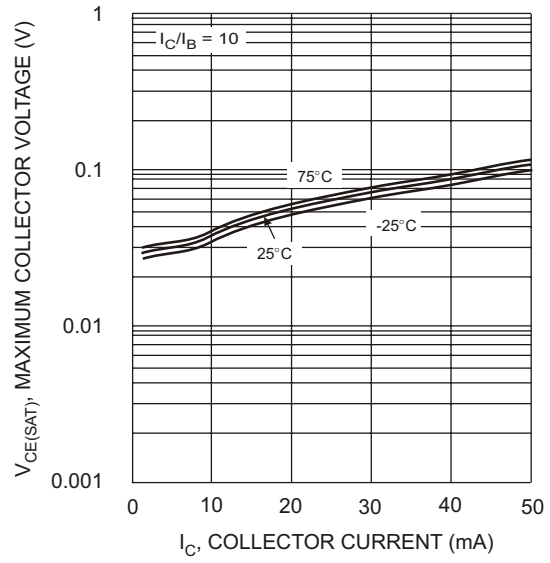


Fig. 2 $V_{CE(SAT)}$ vs. I_C

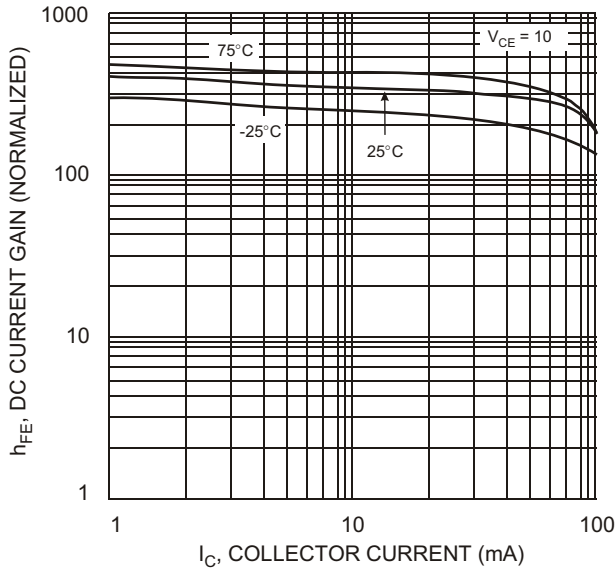


Fig. 3 DC Current Gain

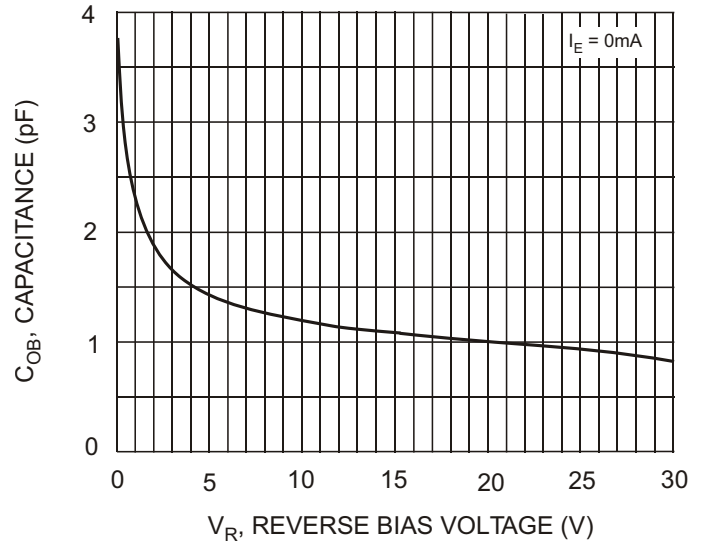


Fig. 4 Output Capacitance

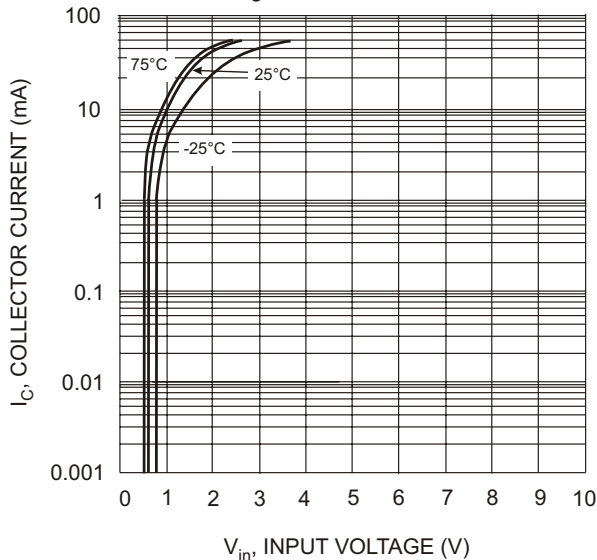


Fig. 5 Collector Current Vs. Input Voltage

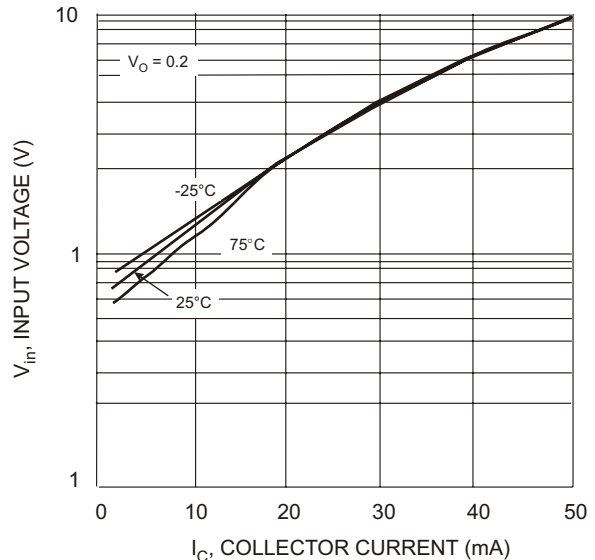


Fig. 6 Input Voltage vs. Collector Current